BLF8G24LS-150V; BLF8G24LS-150GV

$\frac{ \textbf{Power LDMOS transistor}}{ \text{Rev. 1} - 4 \text{ November 2013}}$

Objective data sheet

1. Product profile

1.1 General description

150 W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 2300 MHz to 2400 MHz.

Table 1. **Typical performance**

Typical RF performance at T_{case} = 25 °C in a common source class-AB production test circuit.

Test signal	f	I _{Dq}	V _{DS}	P _{L(AV)}	Gp	η_{D}	ACPR _{5M}
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2300 to 2400	1300	28	45	18	30	-30 ^[1]

^{[1] 3}GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz. Channel bandwidth is 3.84 MHz.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth (60 MHz typical)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Design optimized for gull-wing
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

RF power amplifiers for W-CDMA base stations and multi carrier applications in the 2300 MHz to 2400 MHz frequency range



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF8G24	4LS-150V (SOT1244B)		
1	drain		
2	gate	4 1 5	6.7→1 → 4,5
3	source [6,7
4	decoupling lead	3	3
5	decoupling lead		aaa-003619
6	n.c.		
7	n.c.	6 2 7	
BLF8G24	4LS-150GV (SOT1244C)	
1	drain		
2	gate	- 4 1 5 	6.7→1 → 4.5
3	source [11	6,7
4	decoupling lead		3
5	decoupling lead		aaa-003619
6	n.c.	6 2 7 3	
7	n.c.		

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package					
	Name	Description	Version				
BLF8G24LS-150V	-	earless flanged ceramic package; 6 leads	SOT1244B				
BLF8G24LS-150GV	-	earless flanged ceramic package; 6 leads	SOT1244C				

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		[1] -	225	°C

^[1] Continuous use at maximum temperature will affect the reliability.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 45 W	0.30	K/W

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C unless otherwise specified.

Parameter	Conditions	Min	Тур	Max	Unit
drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.16 \text{ mA}$	65	-	-	V
gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 216 \text{ mA}$	1.5	1.9	2.3	V
drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	4.5	μΑ
drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	40	-	Α
gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	450	nΑ
forward transconductance	$V_{DS} = 10 \text{ V}; I_{D} = 10.8 \text{ A}$	-	16	-	S
drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 7.56 \text{ A}$	-	0.06	-	Ω
	drain-source breakdown voltage gate-source threshold voltage drain leakage current drain cut-off current gate leakage current forward transconductance	$\begin{array}{ll} \text{drain-source breakdown voltage} & \text{V}_{GS} = 0 \text{ V; I}_D = 2.16 \text{ mA} \\ \text{gate-source threshold voltage} & \text{V}_{DS} = 10 \text{ V; I}_D = 216 \text{ mA} \\ \text{drain leakage current} & \text{V}_{GS} = 0 \text{ V; V}_{DS} = 28 \text{ V} \\ \text{drain cut-off current} & \text{V}_{GS} = \text{V}_{GS(\text{th})} + 3.75 \text{ V; } \\ \text{V}_{DS} = 10 \text{ V} \\ \text{gate leakage current} & \text{V}_{GS} = 11 \text{ V; V}_{DS} = 0 \text{ V} \\ \text{forward transconductance} & \text{V}_{DS} = 10 \text{ V; I}_D = 10.8 \text{ A} \\ \text{drain-source on-state resistance} & \text{V}_{GS} = \text{V}_{GS(\text{th})} + 3.75 \text{ V;} \\ \end{array}$	$\begin{array}{llllllllllllllllllllllllllllllllllll$	$\begin{array}{llllllllllllllllllllllllllllllllllll$	$\begin{array}{llllllllllllllllllllllllllllllllllll$

Table 7. RF characteristics

Test signal: 2-carrier W-CDMA, 3GPP test model; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on the CCDF, carrier spacing 5 MHz; f_1 = 2302.5 MHz; f_2 = 2307.5 MHz; f_3 = 2392.5 MHz; f_4 = 2397.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 1300 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G_p	power gain	$P_{L(AV)} = 45 \text{ W}$	<tbd></tbd>	18	-	dB
RL_{in}	input return loss	$P_{L(AV)} = 45 \text{ W}$	-	-10	<tbd></tbd>	dB
η_{D}	drain efficiency	$P_{L(AV)} = 45 \text{ W}$	<tbd></tbd>	30	-	%
ACPR _{5M}	adjacent channel power ratio (5 MHz)	$P_{L(AV)} = 45 \text{ W}$	-	-30	<tbd></tbd>	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLF8G24LS-150V and BLF8G24LS-150GV are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 28 \text{ V}$; $I_{Dq} = 1300 \text{ mA}$; $P_L = 150 \text{ W}$ (CW); f = 2300 MHz.

8. Package outline

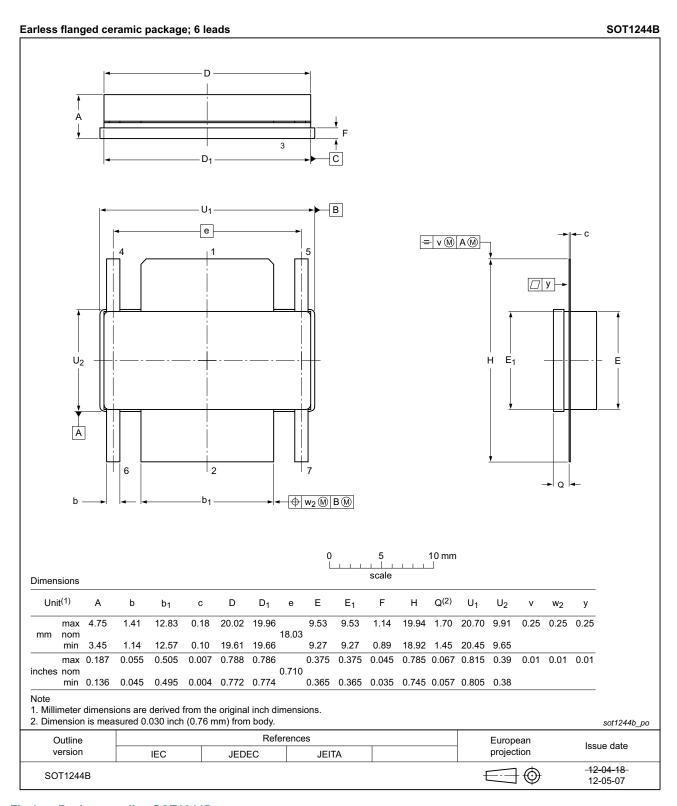


Fig 1. Package outline SOT1244B

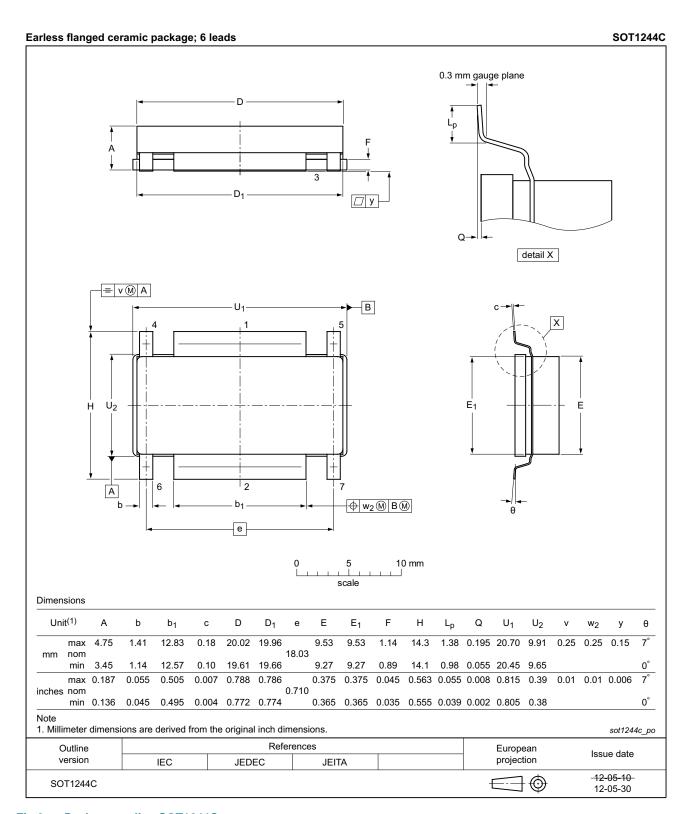


Fig 2. Package outline SOT1244C

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 8. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
PAR	Peak-to-Average Ratio
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF8G24LS-150V_8G24LS-150GV v.1	20131104	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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BLF8G24LS-150(G)V

Power LDMOS transistor

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